# 1. General description

NPN high-voltage low  $V_{CEsat}$  Breakthrough In Small Signal (BISS) transistor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

## 2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_{\text{C}}$  and  $I_{\text{CM}}$
- High collector current gain (h<sub>FE</sub>) at high I<sub>C</sub>
- AEC-Q101 qualified

# 3. Applications

- Electronic ballasts
- LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- · Flyback converters
- Switch Mode Power Supply (SMPS)

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	500	V
I <sub>C</sub>	collector current		-	-	150	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = 10 \text{ V}; I_{C} = 30 \text{ mA}; T_{amb} = 25 \text{ °C}$	50	100	-	

# 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base	3 2 1	B — [
			SOT89	sym123



## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

# 6. Ordering information

#### **Table 3. Ordering information**

Type number Package						
	Name	Description	Version			
PBHV8550X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBHV8550X	C8

# 8. Limiting values

### Table 5. Limiting values

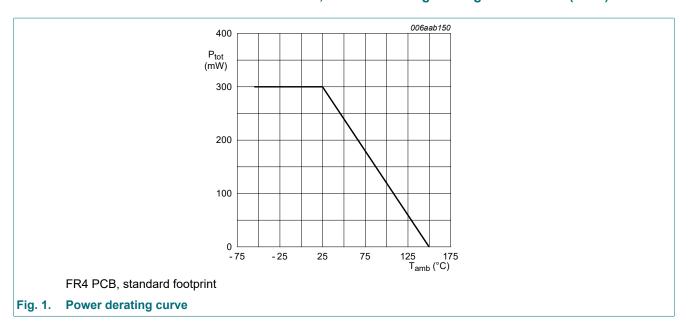
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	500	V
$V_{CEO}$	collector-emitter voltage	open base		-	500	V
V <sub>CESM</sub>	collector-emitter peak voltage	V <sub>BE</sub> = 0 V		-	500	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	6	V
I <sub>C</sub>	collector current			-	150	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	0.5	А
I <sub>BM</sub>	peak base current			-	200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	520	mW
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm <sup>2</sup>.

### 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

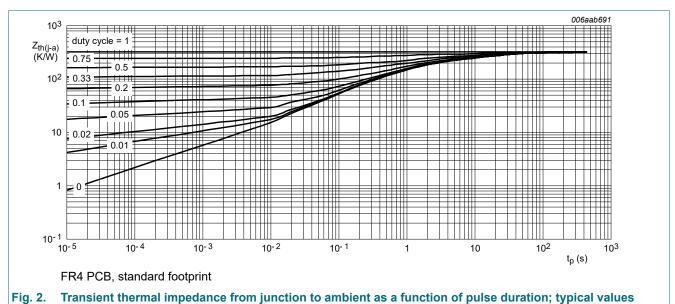


## 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from	in free air	[1]	-	-	241	K/W
	junction to ambient		[2]	-	-	84	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	20	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>.



## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

# 10. Characteristics

#### **Table 7. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	500	-	-	V
V <sub>(BR)CES</sub>	collector-emitter breakdown voltage (base shorted)	$I_C = 2.5 \text{ mA}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	500	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	$I_E = 100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	6	-	-	V
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 360 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
	current	V <sub>CB</sub> = 360 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	50	μA
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 360 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 10 V; I <sub>C</sub> = 30 mA; T <sub>amb</sub> = 25 °C	50	100	-	
		$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; $t_{p} \le 300 \mu s$ ; pulsed; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	50	100	-	
V <sub>CEsat</sub>	collector-emitter	$I_C$ = 20 mA; $I_B$ = 2 mA; $T_{amb}$ = 25 °C	-	60	75	mV
	saturation voltage	$I_C$ = 50 mA; $I_B$ = 6 mA; $t_p \le 300 \mu s$ ; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	65	90	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = 50 mA; $I_B$ = 5 mA; $t_p \le 300 \mu s$ ; pulsed; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	0.75	0.9	V
t <sub>d</sub>	delay time	V <sub>CC</sub> = 20 V; I <sub>C</sub> = 0.05 A; I <sub>Bon</sub> = 5 mA;	-	80	-	ns
t <sub>r</sub>	rise time	I <sub>Boff</sub> = -5 mA; T <sub>amb</sub> = 25 °C	-	2700	-	ns
t <sub>on</sub>	turn-on time		-	2780	-	ns
t <sub>s</sub>	storage time		-	3400	-	ns
t <sub>f</sub>	fall time		-	800	-	ns
t <sub>off</sub>	turn-off time		-	4200	-	ns
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 10 mA; f = 100 MHz; $T_{amb}$ = 25 °C	-	35	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$	-	4	-	pF
C <sub>e</sub>	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	200	-	pF

### 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

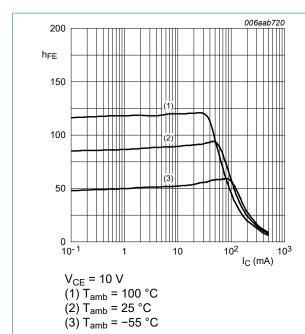


Fig. 3. DC current gain as a function of collector current; typical values

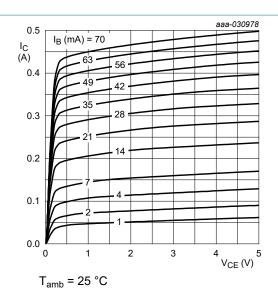


Fig. 4. Collector current as a function of collectoremitter voltage; typical values

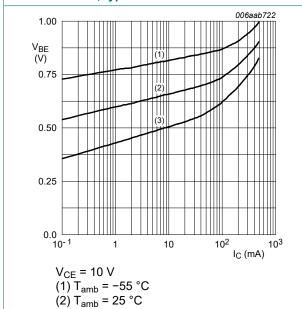
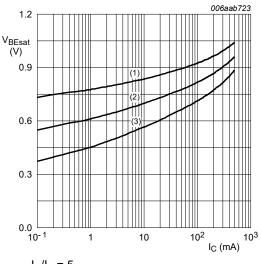


Fig. 5. Base-emitter voltage as a function of collector current; typical values

(3)  $T_{amb} = 100 \, ^{\circ}C$ 



 $I_{\rm C}/I_{\rm B} = 5$ (1)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = 100~{\rm ^{\circ}C}$ 

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

### 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

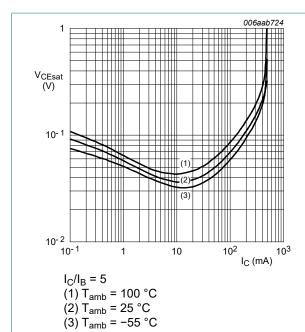


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

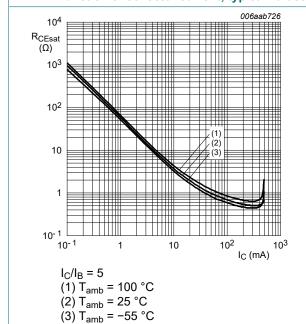


Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values

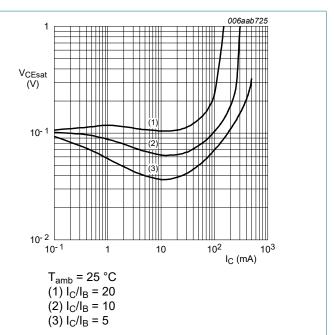


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

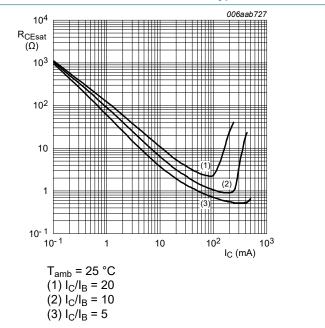
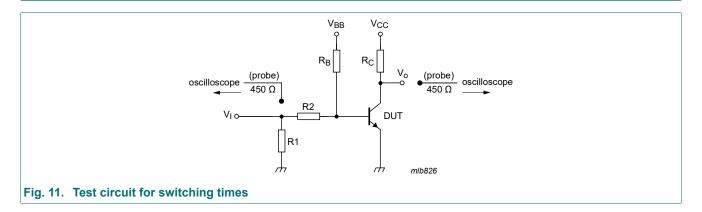


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

# 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

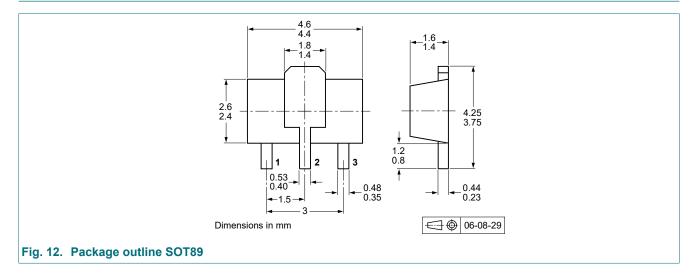
# 11. Test information



### **Quality information**

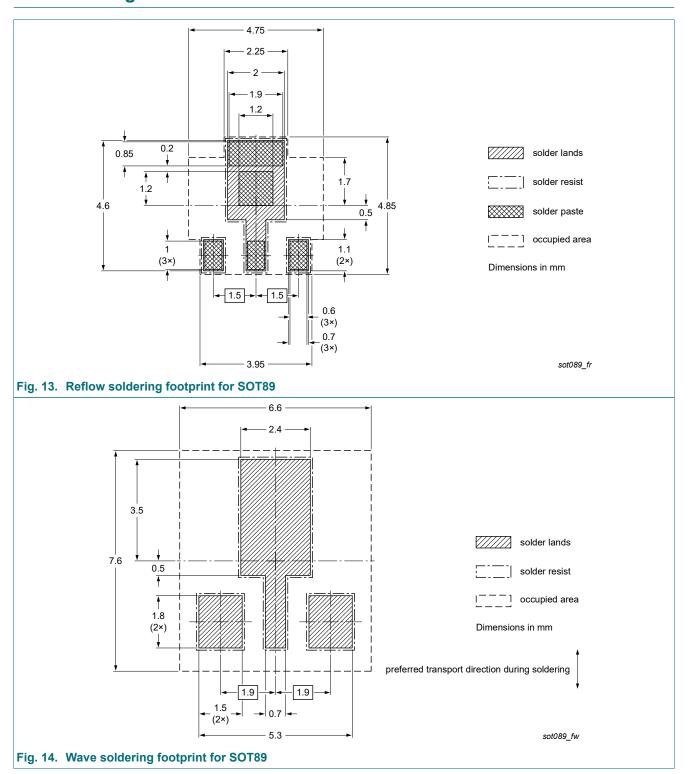
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 12. Package outline



## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

# 13. Soldering



## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

# 14. Revision history

## Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8550X v.3	20200608	Product data sheet	-	PBHV8550X v.2
Modifications:	Figure 4 updated wit	h additional curves		
PBHV8550X v.2	20200214	Objective data sheet	-	PBHV8550X v.1
PBHV8550X v.1	20200130	Objective data sheet	-	-

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#### 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

# 15. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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## 500 V, 150 mA NPN high-voltage low VCEsat (BISS) transistor

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Date of release: 8 June 2020

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